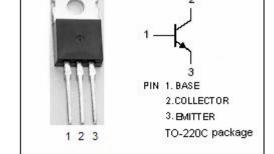


isc Silicon NPN Power Transistor

MJE2360T

DESCRIPTION

- · Collector-Emitter Sustaining Voltage-
- : $V_{CEO(SUS)} = 350 \text{ V(Min)}$
- DC Current Gain-
 - : h_{FE} = 25(Min) @ I_C= 50mA
- Low Collector Saturation Voltage
- : V_{CE(sat)} = 1.5V(Max.)@ I_C= 100mA
- Minimum Lot-to-Lot variations for robust device performance and reliable operation



APPLICATIONS

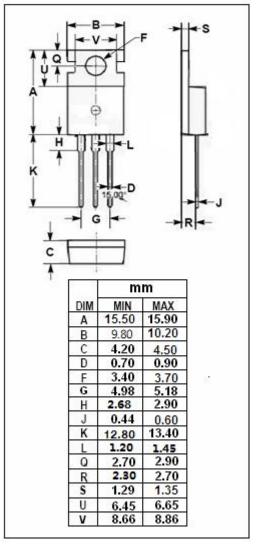
• Designed for low power audio amplifier and low-current, high-speed switching applications.

ABSOLUTE MAXIMUM RATINGS(Ta=25°C)

| SYMBOL | PARAMETER | VALUE | UNIT |
|------------------|--|---------|------------|
| V _{CEO} | Collector-Emitter Voltage | 350 | V |
| V _{CEV} | Collector-Emitter Voltage | 375 | V |
| V _{EBO} | Emitter-Base Voltage | 6 | V |
| Ic | Collector Current-Continuous | 0.5 | А |
| I _{CM} | Collector Current-Peak | 1 | Α |
| I _B | Base Current | 0.25 | А |
| Pc | Collector Power Dissipation T _a =25°C | 0.24 | 10/ |
| | Collector Power Dissipation T _C =25°C | 30 | W |
| TJ | Junction Temperature | -65~150 | $^{\circ}$ |
| T _{stg} | Storage Temperature Range | -65~150 | $^{\circ}$ |

THERMAL CHARACTERISTICS

| SYMBOL | PARAMETER | MAX | UNIT |
|---------------------|-------------------------------------|-------|------|
| R _{th j-c} | Thermal Resistance,Junction to Case | 4.167 | °C/W |





isc Silicon NPN Power Transistor

MJE2360T

ELECTRICAL CHARACTERISTICS

T_C =25℃ unless otherwise specified

| SYMBOL | PARAMETER | CONDITIONS | MIN | MAX | UNIT |
|-------------------------|--------------------------------------|---|-----|------|------|
| V _{CEO(SUS)} | Collector-Emitter Sustaining Voltage | I _C = 2.5mA; I _B = 0 | 350 | | V |
| V _{CE} (sat)-1 | Collector-Emitter Saturation Voltage | I _C = 100mA ;I _B =10mA | | 1.5 | V |
| V _{BE(on)} | Base-Emitter On Voltage | I _C = 100mA; V _{CE} = 10V | | 1 | V |
| I _{CEO} | Collector Cutoff Current | V _{CE} = 250V; IB=0 | | 0.25 | mA |
| I _{CEX} | Collector Cutoff Current | V _{CE} = 375V; V _{BE(off)} = 1.5V | | 0.5 | mA |
| I _{CBO} | Collector Cutoff Current | V _{CB} = 375V; I _E = 0 | | 0.1 | mA |
| I _{EBO} | Emitter Cutoff Current | V _{EB} = 5V; I _C = 0 | | 0.1 | mA |
| h _{FE-1} | DC Current Gain | I _C = 50m A; V _{CE} = 10V | 25 | 200 | |
| h _{FE-2} | DC Current Gain | I _C = 100mA ; V _{CE} = 10V | 15 | | |

NOTICE:

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